

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	"20050110054"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/02/13 12:11
S2	11	("20020171076" "5116774" "5241197" "5389554" "5598211" "6034386" "6078067" "6144048" "6194747" "6452221" "6620662").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/16 19:02
S3	8	("5635735" "5760427" "5949095" "6144048" "6242766" "6255673" "6281528" "6294801").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/16 18:50
S4	3	("4615102" "4733283" "5021857").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/16 18:54
S5	4	("6078067").URPN.	USPAT	OR	ON	2005/09/16 18:59
S6	2	"06120258"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/16 18:59
S7	1	wohlmuth-walter-anthony.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/16 19:02
S8	347	((deplet\$3 adj mode) or D-mode) and ((enhance\$4 adj mode) or E-mode) and substrate and isolat\$3 and (schottky or silicid \$3 or salicid\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/11/12 13:36
S9	46	S8 and barrier and (etch\$3 adj2 (barrier or stop)) and gate and source and drain and channel	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/16 19:21
S10	1	S9 and amorphizat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/16 19:48
S11	5	S8 and amorphizat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/16 19:24
S12	44	S9 not (S2 S3 S4 S5 S6 S7 S11)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/16 20:13
S13	2	("4663643" "5959317").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/16 19:30
S14	0	("6670652").URPN.	USPAT	OR	ON	2005/09/16 19:30
S15	10	("3764865" "3855690" "3861024" "3943622" "4961194" "5445985" "5633183" "5698870" "5698900" "5766967").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/16 19:31

S16	2	("6222210").URPN.	USPAT	OR	ON	2005/09/16 19:34
S17	1	("5068756").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/16 19:38
S18	13	("5243207").URPN.	USPAT	OR	ON	2005/09/16 19:38
S19	5	S8 and amorphizat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/16 19:48
S20	237	((((deplet\$3 adj mode) or D-mode or D-type) and ((enhance\$4 adj mode) or E-mode or E-type) with (transistor or "FET"))) and substrate and isolat\$3 and (schottky or silicid\$3 or salicid\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/02/13 12:13
S21	13	((((deplet\$3 adj mode) or D-mode or D-type) and ((enhance\$4 adj mode) or E-mode or E-type)).ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/16 20:09
S22	4	S20 and S21	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/16 20:09
S23	226	S20 not (S2 S3 S4 S5 S6 S7 S11 S13 S15 S16 S17 S18 S19 S21)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/16 20:14
S24	2	S23 and (barrier with amorph\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/16 20:15
S25	60	S23 and (solid adj state)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/16 20:15
S26	16	"5243207"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/13 18:40
S27	2	S26 and ((depletion or (deplet\$3 adj mode) or D-mode or D-type) and (enhance\$5 or (enhance\$4 adj mode) or E-mode or E-type))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/13 18:50
S28	1	("5068756").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/13 19:09
S29	3577	257/54,73,155,205,267-269,280,281,392,437,449,e21.047,e21.189,e21.485,e21.631,e27.061,e27.068,e29.041,e31.074,e33.051,e51.009.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/02/13 18:42
S30	136	S29 and ((deplet\$4 or "DFET" or (D adj FET) or (D adj mode)) same (enhanc\$4 or "EFET" or (E adj FET) or (E adj mode)))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/03 20:55
S31	88	S30 and (ohmic\$3 or schottky or silicid\$3 or salicid\$3 or amorph\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/03 20:40

S32	28	S31 and solid	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/03 20:42
S33	25	S32 and (@ad<"20031124" or @riad<"20031124")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/03 20:46
S34	14	S33 and barrier and channel	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/03 20:51
S35	11	S33 not S34	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/03 20:46
S36	0	(S30 not "20") and (singl\$4 with barrier) and (@ad<"20031124" or @riad<"20031124")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/03 20:47
S37	3	(S30 not S33) and (singl\$4 with barrier) and (@ad<"20031124" or @riad<"20031124")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/03 20:48
S38	90	(S29 not (S33 S37)) and (singl\$4 with barrier) and (@ad<"20031124" or @riad<"20031124")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/03 20:48
S39	17	S38 and (singl\$4 near2 barrier)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/03 20:48
S40	0	(S38 not S39) and (((deplet\$4 or "DFET" or (D adj FET) or (D adj mode)) with (enhanc\$4 or "EFET" or (E adj FET) or (E adj mode)))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/03 20:50
S41	39	(S38 not S39) and barrier and channel	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/03 20:51
S42	16	((((deplet\$4 or "DFET" or (D adj FET) or (D adj mode)) same (enhanc\$5 or "EFET" or (E adj FET) or (E adj mode))) and barrier and channel).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/03 20:55
S43	178	((("D" deplet\$3) near2 (mode transistor FET)) or D-mode or D-type or DFET or D-FET DMOS) and (((("E" enhanc\$3 enhancement) near2 (mode transistor FET)) or E-mode or E-type or EFET or E-FET EMOS) and barrier and (etch\$4 near2 stop\$3) and (source drain) and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/02/13 18:45
S44	16	S43 and (single near2 (barrier etch\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/02/13 12:20

S45	3	((("4635343") or ("4733283"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/02/13 18:17
S46	1343	257/192.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 18:30
S47	199	257/195.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 18:20
S48	5747	257/54,73,192,194,155,205,267- 269,280,281,392,437,449,e21.047,e21.189, e21.485,e21.631,e27.061,e27.068,e29.041, e29.072,e29.061,e31.074,e33.051,e51.009. ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/02/13 18:43
S49	12	H01L29/43.ipc.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/02/13 18:45
S50	84	H01L31/072.ipc.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/02/13 18:44
S51	5	H01L29/161.ipc.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/02/13 18:44
S52	5824	S48 S49 S50 S51	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/02/13 18:45
S53	44	S52 and (((("D" deplet\$3) near2 (mode transistor FET)) or D-mode or D-type or DFET or D-FET DMOS) and (((("E" enhanc\$3 enhancement) near2 (mode transistor FET)) or E-mode or E-type or EFET or E-FET EMOS) and barrier and (etch\$4 near2 stop\$3) and (source drain) and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/02/13 18:51
S54	2	(((("D" deplet\$3) near2 (mode transistor FET)) or D-mode or D-type or DFET or D-FET DMOS) and (((("E" enhanc\$3 enhancement) near2 (mode transistor FET)) or E-mode or E- type or EFET or E-FET EMOS) and barrier and (etch\$4 near2 stop\$3) and (source drain) and gate).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/02/13 18:52
S55	3	(((("D" deplet\$3) near2 (mode transistor FET)) or D-mode or D-type or DFET or D-FET DMOS) and (((("E" enhanc\$3 enhancement) near2 (mode transistor FET)) or E-mode or E- type or EFET or E-FET EMOS) and barrier and (etch\$4 near2 stop\$3)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/02/13 18:52

S56	1206	(((((("D" deplet\$3) near2 (mode transistor FET)) or D-mode or D-type or DFET or D-FET DMOS) and (((("E" enhanc\$3 enhancement) near2 (mode transistor FET)) or E-mode or E-type or EFET or E-FET EMOS)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/02/13 18:53
S57	43	S56 and barrier.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/02/13 18:53
S58	16	S57 and etch\$3.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/02/13 18:53
S59	15	((US-5264390-\$ or US-4760230-\$ or US-5906965-\$ or US-5997681-\$ or US-6136132-\$ or US-4615102-\$ or US-4827321-\$ or US-4860298-\$ or US-4879724-\$ or US-5180911-\$ or US-5252433-\$ or US-5363397-\$ or US-5426016-\$ or US-5841180-\$ or US-4243298-\$).did.	USPAT	OR	ON	2007/02/13 18:56
S60	3	10/721437	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 19:14
S61	114	((deplet\$3 adj mode) or D-mode) and ((enhance\$4 adj mode) or E-mode) and barrier and channel and (etch\$3 adj stop\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/11/12 14:22
S62	5	("20020177261" "5686741" "6274893" "6670652" "6703638").PN. OR ("7183592").URFN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/11/12 13:31
S63	3218	((deplet\$3 adj mode) or D-mode) and ((enhance\$4 adj mode) or E-mode)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/11/12 13:36
S64	681	(S63 not S61) and barrier	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/11/12 13:36
S65	1136	(S63 not S61) and etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/11/12 13:36
S66	446	S64 and S65	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/11/12 14:14
S67	415	S66 and source and drain	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/11/12 14:14
S68	226	257/205.ocls	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/11/12 14:16

S69	557	257/392.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/11/12 14:16
S70	769	((deplet\$3 adj2 mode) or D-mode or (D adj mode)) and ((enhance\$4 adj2 mode) or E-mode or (E adj mode)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/11/12 14:27
S71	18	S70 and (barrier and channel and etch\$3).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/11/12 14:23
S72	502	(S70 not S71) and (source and drain).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/11/12 14:28
S73	26	S72 and barrier.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/11/12 14:28
S74	1543	257/192.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2008/07/23 11:39
S75	593	257/392.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2008/07/23 11:39
S76	234	257/155.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2008/07/23 11:39
S77	7	((("D" deplet\$3) near2 (mode transistor FET)) or D-mode or D-type or DFET or D-FET DMOS) and (((("E" enhanc\$3 enhancement) near2 (mode transistor FET)) or E-mode or E-type or EFET or E-FET EMOS)).clm. and (barrier and etch\$4 near2 stop\$3) and (source drain) and gate).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2008/07/23 11:50
S78	1307	((("D" deplet\$3) near2 (mode transistor FET)) or D-mode or D-type or DFET or D-FET DMOS) and (((("E" enhanc\$3 enhancement) near2 (mode transistor FET)) or E-mode or E-type or EFET or E-FET EMOS)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2008/07/23 11:50
S79	52	S78 and schottky.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2008/07/23 11:51
S80	15	S79 and (gate same barrier).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2008/07/23 11:51
S81	37	S79 not S80	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2008/07/23 11:52

S88	38	S78 and (gate same barrier).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2008/07/23 12:32
S89	3679	((("E" enhanc\$3 enhancement) near2 (mode transistor FET)) or E-mode or E-type or EFET or E-FET EMOS).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2008/07/23 12:33
S90	58	S89 and (gate same barrier).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2008/07/23 12:33
S91	20	S90 not (S79 S88)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2008/07/23 12:34
S92	2	Wohimuth-Walter-Anthony.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2008/07/23 12:35
S93	9	(Triquint adj semiconductor\$3).as. and (((("D" deplet\$3) near2 (mode transistor FET)) or D-mode or D-type or DFET or D-FET DMOS) and (((("E" enhanc\$3 enhancement) near2 (mode transistor FET)) or E-mode or E-type or EFET or E-FET EMOS)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2008/07/23 12:38
S94	10421	(((((("D" deplet\$3) near2 (mode transistor FET)) or D-mode or D-type or DFET or D-FET DMOS) and (((("E" enhanc\$3 enhancement) near2 (mode transistor FET)) or E-mode or E-type or EFET or E-FET EMOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2008/07/23 12:40
S95	947	S94 and (gate same barrier)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2008/07/23 12:41
S96	402	S95 and (gate same schottky)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2008/07/23 12:41
S97	192	S96 and (((("E" enhanc\$3 enhancement) near2 (mode transistor FET)) or E-mode or E-type or EFET or E-FET EMOS) same schottky)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2008/07/23 12:42
S98	138	S97 and (@ad<"20031124" or @riad<"20031124")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2008/07/23 12:43

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